

## Introduction

This technical note discusses memory usage for the iCE40™ device family (iCE40 LP/HX, iCE40LM, iCE40 Ultra™, iCE40 UltraLite™). It is intended to be used as a guide to the high-speed synchronous RAM Blocks and the iCE40 sysMEM™ Embedded Block RAM (EBR). The EBR is the embedded block RAM of the device, each 4 Kbit in size.

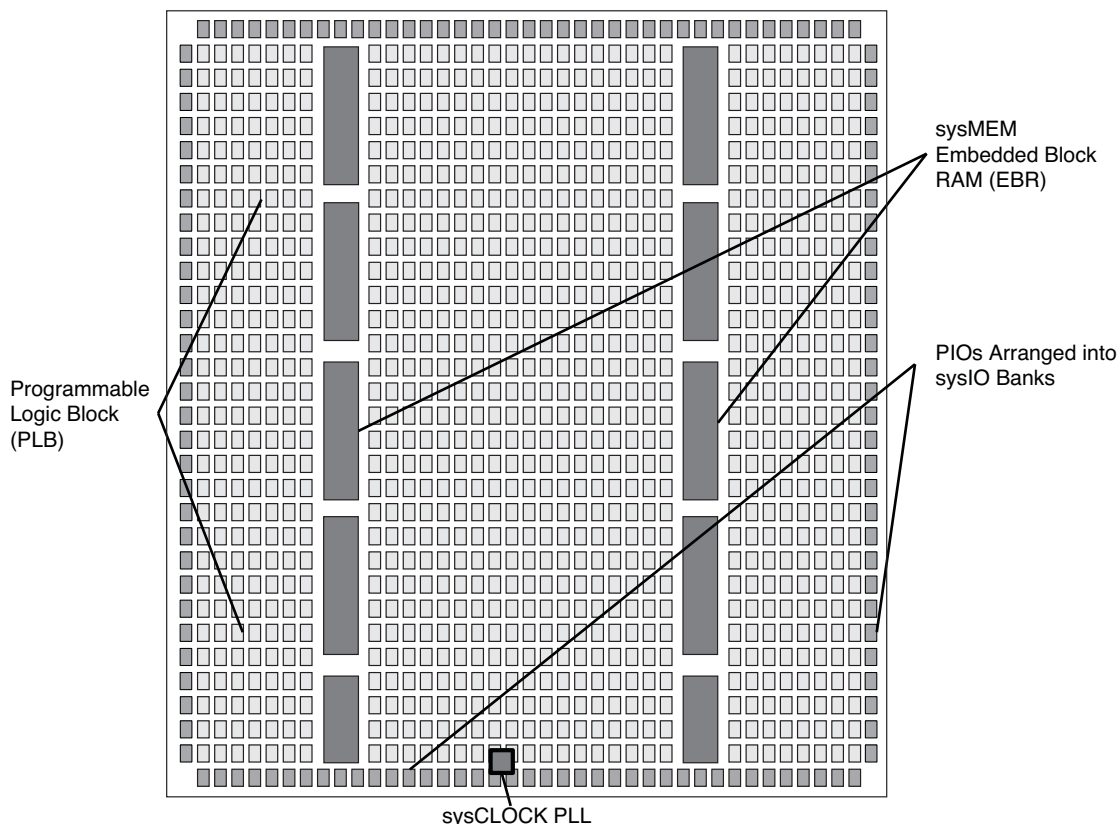
The iCE40 device architecture provides resources for memory-intensive applications. Single-Port RAM, Dual-Port RAM and FIFO can be constructed using the EBRs. The EBRs can be utilized by instantiating software primitives as described later in this document. Apart from primitive instantiation, the iCECube2™ design software infers generic codes as EBRs.

## Memories in iCE40 Devices

iCE40 devices contain an array of EBRs.

Figure 1 shows the placement of EBRs in a typical iCE40 device (does not represent true numbers of design elements).

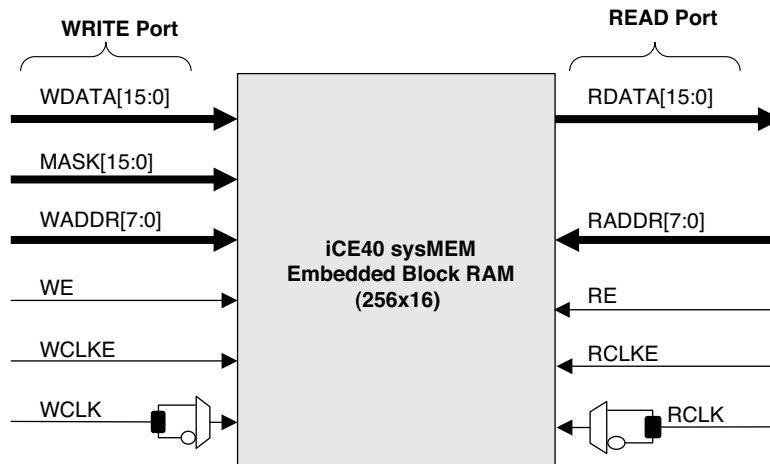
**Figure 1. Typical Layout of an iCE40 Device**



## iCE40 sysMEM Embedded Block RAM

Each iCE40 device includes multiple high-speed synchronous EBRs, each 4Kbit in size. A single iCE40 device integrates between eight and 32 such blocks. Each EBR is a 256-word deep by 16-bit wide, two-port register file, as illustrated in Figure 2. The input and output connections to and from an EBR feed into the programmable interconnect resources.

**Figure 2. sysMEM Embedded Block RAM**



Using programmable logic resources, an EBR implements a variety of logic functions, each with configurable input and output data widths.

- Random-access memory (RAM)
  - Single-port RAM with a common address, enable, and clock control lines
  - Two-port RAM with separate read and write control lines, address inputs, and enable
- Register file and scratchpad RAM
- First-In, First-Out (FIFO) memory for data buffering applications
- 256-deep by 16-wide ROM with registered outputs; contents loaded during configuration
- Counters, sequencers

As shown in Figure 2, an EBR has separate write and read ports, each with independent control signals. Table 1 lists the signals for both ports. Additionally, the write port has an active-low bit-line write-enable control; optionally mask write operations on individual bits. By default, input and output data is 16 bits wide, although the data width is configurable using programmable logic and, if needed, multiple EBRs.

The WCLK and RCLK inputs optionally connect to one of the following clock sources:

- The output from any one of the eight Global Buffers, or
- A connection from the general-purpose interconnect fabric

## Signals

Table 1 lists the signal names, direction, and function of each connection to the EBR block.

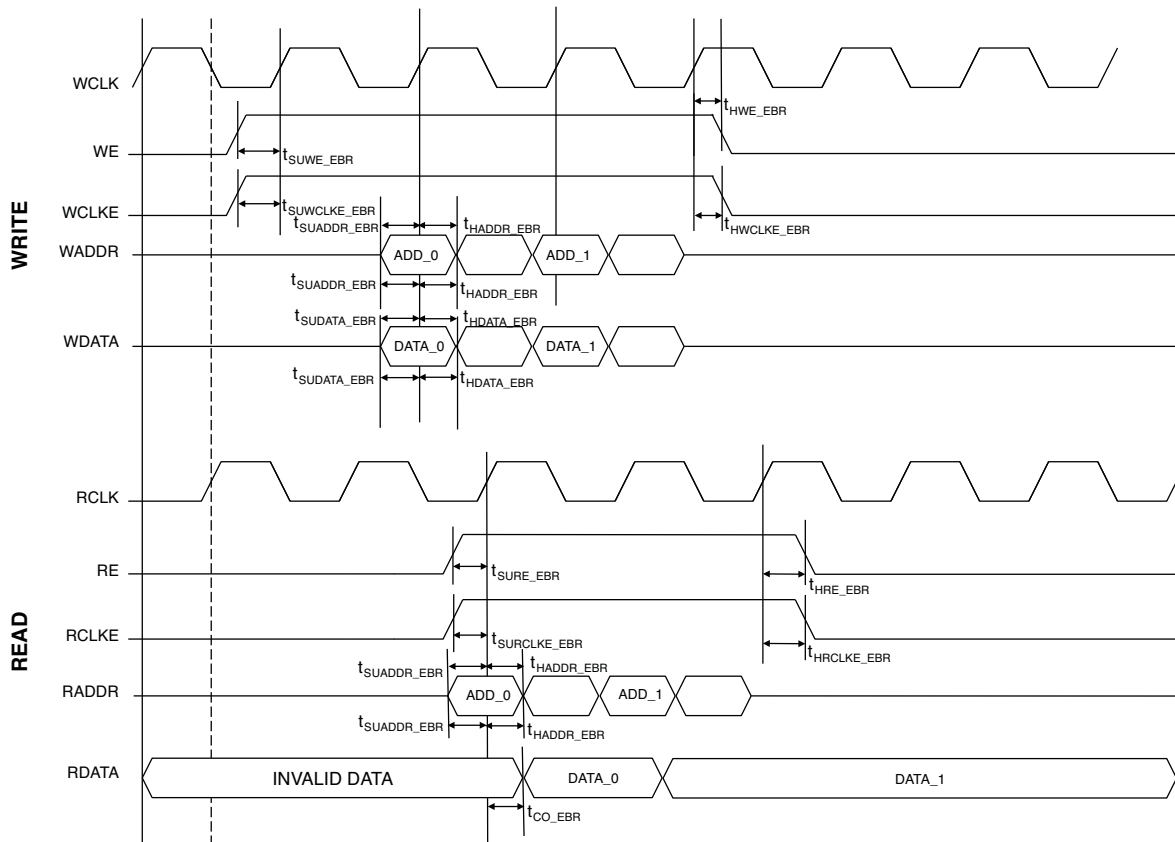
**Table 1. EBR Signal Descriptions**

| Signal Name | Direction | Description   |
|-------------|-----------|---|
| WDATA[15:0] | Input     | Write Data input.   |
| MASK[15:0]  | Input     | Masks write operations for individual data bit-lines.<br>0 = write bit; 1 = don't write bit |
| WADDR[7:0]  | Input     | Write Address input. Selects one of 256 possible RAM locations.                             |
| WE          | Input     | Write Enable input.   |
| WCLKE       | Input     | Write Clock Enable input.   |
| WCLK        | Input     | Write Clock input. Default rising-edge, but with falling-edge option.                       |
| RDATA[15:0] | Output    | Read Data output.   |
| RADDR[7:0]  | Input     | Read Address input. Selects one of 256 possible RAM locations.                              |
| RE          | Input     | Read Enable input. Only available for SB_RAM256x16 configurations.                          |
| RCLKE       | Input     | Read Clock Enable input.  |
| RCLK        | Input     | Read Clock input. Default rising-edge, but with falling-edge option.                        |

## Timing Diagram

Figure 3 shows the timing diagram for the EBR memory module.

**Figure 3. EBR Module Timing Diagram<sup>1</sup>**



1. Internal timing values are considered in the iCEcube2 software's place and route.

---

## Write Operations

By default, all EBR write operations are synchronized to the rising edge of WCLK although the clock is invertible as shown in Figure 2. When the WCLKE signal is low, the clock to the EBR block is disabled, keeping the EBR in its lowest power mode.

To write data into the EBR block, perform the following operations:

- Supply a valid address on the WADDR[7:0] address input port
- Supply valid data on the WDATA[15:0] data input port
- To write or mask selected data bits, set the associated MASK input port accordingly. For example, write operations on data bit D[i] are controlled by the associated MASK[i] input.
  - MASK[i] = 0: Write operations are enabled for data line WDATA[i]
  - MASK[i] = 1: Mask write operations are disabled for data line WDATA[i]
- Enable the EBR write port (WE = 1)
- Enable the EBR write clock (WCLKE = 1)
- Apply a rising clock edge on WCLK (assuming that the clock is not inverted)

## Read Operations

By default, all EBR read operations are synchronized to the rising edge of RCLK although the clock is invertible as shown in Figure 2.

To read data from the EBR block, perform the following operations:

- Supply a valid address on the RADDR[7:0] address input port
- Enable the EBR read port (RE = 1)
- Enable the EBR read clock (RCLKE = 1)
- Apply a rising clock edge on RCLK
- After the clock edge, the EBR contents located at the specified address (RADDR) appear on the RDATA output port

## EBR Considerations

### Read Data Register Undefined Immediately After Configuration

Unlike the flip-flops in the Programmable Logic Blocks and Programmable I/O pins, the RDATA port is not automatically reset after configuration. Consequently, immediately following configuration and before the first valid Read Data operation, the initial RDATA read value is undefined.

### Pre-loading EBR Data

The data contents for an EBR block can be optionally pre-loaded during iCE40 configuration. If not pre-loaded during configuration, then the EBR contents must be initialized by the iCE40 application before the EBR contents are valid. EBR initialization data can be done in the RTL code. Pre-loading the EBR data in the configuration bitstream increases the size of the configuration image accordingly.

### EBR Contents Preserved During Configuration

EBR contents are preserved (write protected) during configuration, assuming that voltage supplies are maintained throughout. Consequently, data can be passed between multiple iCE40 configurations by leaving it in an EBR block and then skipping pre-loading during the subsequent reconfiguration.

## Low-Power Setting

To place an EBR block in its lowest power mode, keep WCLKE = 0 and RCLKE = 0. In other words, when not actively using an EBR block, disable the clock inputs.

## iCE40 sysMEM Embedded Block RAM Memory Primitives

This section lists the iCE40 sysMEM EBR software primitives that can be instantiated in the RTL. Different EBRs are used in different configurations. Each EBR has separate write and read ports, each with independent control signals. Each EBR can be configured into a RAM block of size 256x16, 512x8, 1024x4 or 2048x2. The data contents of the EBR can optionally be pre-loaded during iCE40 device configuration by specifying the initialization data in the primitive instantiation.

Table 2 lists the supported dual port synchronous RAM configurations, each of 4Kbits in size. The RAM blocks can be directly instantiated in the top module and taken through the iCube2 software flow.

**Table 2. EBR Configurations and Primitive Names**

| Block RAM Configuration  | Block RAM Configuration and Size | WADDR Port Size (Bits) | WDATA Port Size (Bits) | RADDR Port Size (Bits) | RDATA Port Size (Bits) | MASK Port Size (Bits) |
|--|----------------------------------|------------------------|------------------------|------------------------|------------------------|-----------------------|
| SB_RAM256x16<br>SB_RAM256x16NR<br>SB_RAM256x16NW<br>SB_RAM256x16NRNW | 256 x 16 (4K)                    | 8 [7:0]                | 16 [15:0]              | 8 [7:0]                | 16 [15:0]              | 16 [15:0]             |
| SB_RAM512x8<br>SB_RAM512x8NR<br>SB_RAM512x8NW<br>SB_RAM512x8NRNW     | 512 x 8 (4K)                     | 9 [8:0]                | 8 [7:0]                | 9 [8:0]                | 8 [7:0]                | No Mask Port          |
| SB_RAM1024x4<br>SB_RAM1024x4NR<br>SB_RAM1024x4NW<br>SB_RAM1024x4NRNW | 1024 x 4 (4K)                    | 10 [9:0]               | 4 [3:0]                | 10 [9:0]               | 4 [3:0]                | No Mask Port          |
| SB_RAM2048x2<br>SB_RAM2048x2NR<br>SB_RAM2048x2NW<br>SB_RAM2048x2NRNW | 2048 x 2 (4K)                    | 11 [10:0]              | 2 [1:0]                | 11 [10:0]              | 2 [1:0]                | No Mask Port          |

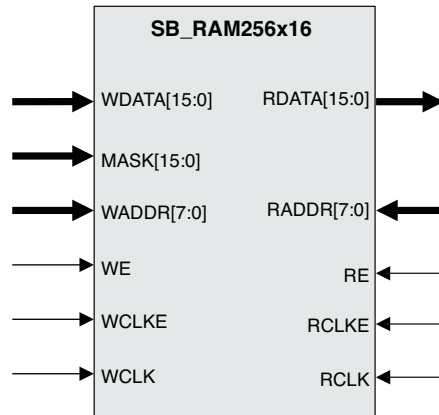
For iCE40 EBR primitives with a negative-edged read or write clock, the base primitive name is appended with a 'N' and a 'R' or 'W' depending on the clock that is affected (see Table 3 for the 256x16 RAM block configuration).

**Table 3. Naming Convention for RAM Primitives**

| RAM Primitive Name | Description   |
|--------------------|---|
| SB_RAM256x16       | Positive-edged read clock, positive-edged write clock |
| SB_RAM256x16NR     | Negative-edged read clock, positive-edged write clock |
| SB_RAM256x16NW     | Positive-edged read clock, negative-edged write clock |
| SB_RAM256x16NRNW   | Negative-edged read clock, negative-edged write clock |

## SB\_RAM256x16

Figure 4. SB\_RAM256x16 Primitive



### Verilog Instantiation

```
SB_RAM256x16 ram256X16_inst (
    .RDATA(RDATA_c[15:0]),
    .RADDR(RADDR_c[7:0]),
    .RCLK(RCLK_c),
    .RCLKE(RCLKE_c),
    .RE(RE_c),
    .WADDR(WADDR_c[7:0]),
    .WCLK(WCLK_c),
    .WCLKE(WCLKE_c),
    .WDATA(WDATA_c[15:0]),
    .WE(WE_c),
    .MASK(MASK_c[15:0])
);

defparam ram256x16_inst.INIT_0 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram256x16_inst.INIT_1 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram256x16_inst.INIT_2 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram256x16_inst.INIT_3 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram256x16_inst.INIT_4 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram256x16_inst.INIT_5 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram256x16_inst.INIT_6 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram256x16_inst.INIT_7 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram256x16_inst.INIT_8 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram256x16_inst.INIT_9 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram256x16_inst.INIT_A =
256'h0000000000000000000000000000000000000000000000000000000000000000;
```

```
defparam ram256x16_inst.INIT_B =  
256'h0000000000000000000000000000000000000000000000000000000000000000;  
defparam ram256x16_inst.INIT_C =  
256'h0000000000000000000000000000000000000000000000000000000000000000;  
defparam ram256x16_inst.INIT_D =  
256'h0000000000000000000000000000000000000000000000000000000000000000;  
defparam ram256x16_inst.INIT_E =  
256'h0000000000000000000000000000000000000000000000000000000000000000;  
defparam ram256x16_inst.INIT_F =  
256'h0000000000000000000000000000000000000000000000000000000000000000;
```

### VHDL Instantiation

```
ram256X16_inst : SB_RAM256x16  
generic map (  
  INIT_0 => X"0000000000000000000000000000000000000000000000000000000000000000",  
  INIT_1 => X"0000000000000000000000000000000000000000000000000000000000000000",  
  INIT_2 => X"0000000000000000000000000000000000000000000000000000000000000000",  
  INIT_3 => X"0000000000000000000000000000000000000000000000000000000000000000",  
  INIT_4 => X"0000000000000000000000000000000000000000000000000000000000000000",  
  INIT_5 => X"0000000000000000000000000000000000000000000000000000000000000000",  
  INIT_6 => X"0000000000000000000000000000000000000000000000000000000000000000",  
  INIT_7 => X"0000000000000000000000000000000000000000000000000000000000000000",  
  INIT_8 => X"0000000000000000000000000000000000000000000000000000000000000000",  
  INIT_9 => X"0000000000000000000000000000000000000000000000000000000000000000",  
  INIT_A => X"0000000000000000000000000000000000000000000000000000000000000000",  
  INIT_B => X"0000000000000000000000000000000000000000000000000000000000000000",  
  INIT_C => X"0000000000000000000000000000000000000000000000000000000000000000",  
  INIT_D => X"0000000000000000000000000000000000000000000000000000000000000000",  
  INIT_E => X"0000000000000000000000000000000000000000000000000000000000000000",  
  INIT_F => X"0000000000000000000000000000000000000000000000000000000000000000"  
)  
  
port map (  
  RDATA => RDATA_c,  
  RADDR => RADDR_c,  
  RCLK => RCLK_c,  
  RCLKE => RCLKE_c,  
  RE => RE_c,  
  WADDR => WADDR_c,  
  WCLK=> WCLK_c,  
  WCLKE => WCLKE_c,  
  WDATA => WDATA_c,  
  MASK => MASK_c,  
  WE => WE_c  
);
```

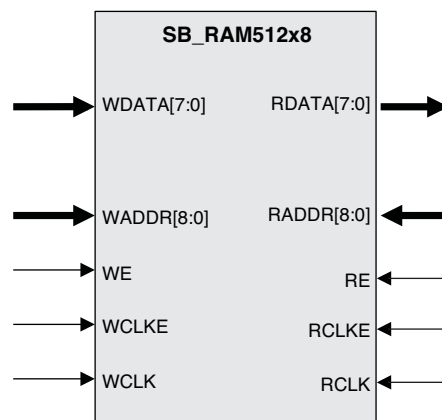
Table 4 is a complete list of SB\_RAM256x16 based primitives.

**Table 4. SB\_RAM256x16 Based Primitives**

| Primitive        | Description   |
|------------------|---|
| SB_RAM256x16     | SB_RAM256x16 //Positive edged clock RCLK WCLK (RDATA, RCLK, RCLKE, RE, RADDR, WCLK, WCLKE, WE, WADDR, MASK, WDATA);                           |
| SB_RAM256x16NR   | SB_RAM256x16NR // Negative edged Read Clock – i.e. RCLKN (RDATA, RCLKN, RCLKE, RE, RADDR, WCLK, WCLKE, WE, WADDR, MASK, WDATA);               |
| SB_RAM256x16NW   | SB_RAM256x16NW // Negative edged Write Clock – i.e. WCLKN (RDATA, RCLK, RCLKE, RE, RADDR, WCLKN, WCLKE, WE, WADDR, MASK, WDATA);              |
| SB_RAM256x16NRNW | SB_RAM256x16NRNW // Negative edged Read and Write – i.e. RCLKN WRCLKN (RDATA, RCLKN, RCLKE, RE, RADDR, WCLKN, WCLKE, WE, WADDR, MASK, WDATA); |

## SB\_RAM512x8

**Figure 5. SB\_RAM512x8 Primitive**



### Verilog Instantiation

```
SB_RAM512x8 ram512X8_inst (
    .RDATA(RDATA_c[7:0]),
    .RADDR(RADDR_c[8:0]),
    .RCLK(RCLK_c),
    .RCLKE(RCLKE_c),
    .RE(RE_c),
    .WADDR(WADDR_c[8:0]),
    .WCLK(WCLK_c),
    .WCLKE(WCLKE_c),
    .WDATA(WDATA_c[7:0]),
    .WE(WE_c)
);

defparam ram512x8_inst.INIT_0 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram512x8_inst.INIT_1 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram512x8_inst.INIT_2 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram512x8_inst.INIT_3 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram512x8_inst.INIT_4 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
```



```
defparam ram512x8_inst.INIT_5 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram512x8_inst.INIT_6 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram512x8_inst.INIT_7 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram512x8_inst.INIT_8 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram512x8_inst.INIT_9 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram512x8_inst.INIT_A =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram512x8_inst.INIT_B =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram512x8_inst.INIT_C =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram512x8_inst.INIT_D =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram512x8_inst.INIT_E =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram512x8_inst.INIT_F =
256'h0000000000000000000000000000000000000000000000000000000000000000;
```

#### VHDL Instantiation

```
ram512X8_inst : SB_RAM512x8
```

```
generic map (
```

```
INIT_0 => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_1 => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_2 => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_3 => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_4 => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_5 => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_6 => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_7 => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_8 => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_9 => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_A => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_B => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_C => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_D => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_E => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_F => X"0000000000000000000000000000000000000000000000000000000000000000"
)
```

```
port map (
```

```
  RDATA => RDATA_c,
  RADDR => RADDR_c,
  RCLK => RCLK_c,
  RCLKE => RCLKE_c,
  RE => RE_c,
  WADDR => WADDR_c,
  WCLK => WCLK_c,
  WCLKE => WCLKE_c,
  WDATA => WDATA_c,
```

```
WE => WE_c
);
WE => WE_c
);
```

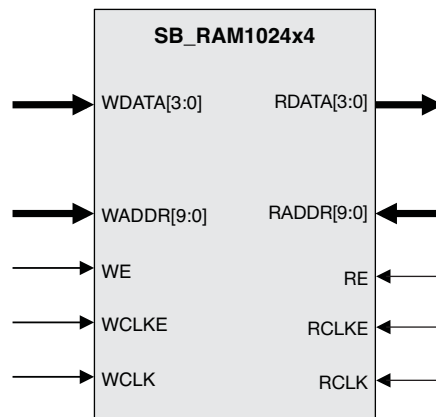
Table 5 is a complete list of SB\_RAM512x8 based primitives.

**Table 5. SB\_RAM512x8 Based Primitives**

| Primitive       | Description  |
|-----------------|--|
| SB_RAM512x8     | SB_RAM512x8 //Positive edged clock RCLK WCLK (RDATA, RCLK, RCLKE, RE, RADDR, WCLK, WCLKE, WE, WADDR, MASK, WDATA);                           |
| SB_RAM512x8NR   | SB_RAM512x8NR // Negative edged Read Clock – i.e. RCLKN (RDATA, RCLKN, RCLKE, RE, RADDR, WCLK, WCLKE, WE, WADDR, MASK, WDATA);               |
| SB_RAM512x8NW   | SB_RAM512x8NW // Negative edged Write Clock – i.e. WCLKN (RDATA, RCLK, RCLKE, RE, RADDR, WCLKN, WCLKE, WE, WADDR, MASK, WDATA);              |
| SB_RAM512x8NRNW | SB_RAM512x8NRNW // Negative edged Read and Write – i.e. RCLKN WRCLKN (RDATA, RCLKN, RCLKE, RE, RADDR, WCLKN, WCLKE, WE, WADDR, MASK, WDATA); |

## SB\_RAM1024x4

**Figure 6. SB\_RAM1024x4 Primitive**



## Verilog Instantiation

```
SB_RAM1024x4 ram1024x4_inst (
    .RDATA(RDATA_c[3:0]),
    .RADDR(RADDR_c[9:0]),
    .RCLK(RCLK_c),
    .RCLKE(RCLKE_c),
    .RE(RE_c),
    .WADDR(WADDR_c[3:0]),
    .WCLK(WCLK_c),
    .WCLKE(WCLKE_c),
    .WDATA(WDATA_c[9:0]),
    .WE(WE_c)
);

defparam ram1024x4_inst.INIT_0 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram1024x4_inst.INIT_1 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
```

```
defparam ram1024x4_inst.INIT_2 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram1024x4_inst.INIT_3 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram1024x4_inst.INIT_4 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram1024x4_inst.INIT_5 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram1024x4_inst.INIT_6 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram1024x4_inst.INIT_7 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram1024x4_inst.INIT_8 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram1024x4_inst.INIT_9 =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram1024x4_inst.INIT_A =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram1024x4_inst.INIT_B =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram1024x4_inst.INIT_C =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram1024x4_inst.INIT_D =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram1024x4_inst.INIT_E =
256'h0000000000000000000000000000000000000000000000000000000000000000;
defparam ram1024x4_inst.INIT_F =
256'h0000000000000000000000000000000000000000000000000000000000000000;
```

### VHDL Instantiation

Ram1024X4\_inst : SB\_RAM1024x4

```
generic map (
INIT_0 => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_1 => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_2 => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_3 => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_4 => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_5 => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_6 => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_7 => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_8 => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_9 => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_A => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_B => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_C => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_D => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_E => X"0000000000000000000000000000000000000000000000000000000000000000",
INIT_F => X"0000000000000000000000000000000000000000000000000000000000000000"
)
```

```
port map (
RDATA => RDATA_c,
RADDR => RADDR_c,
RCLK => RCLK_c,
```

```
RCLKE => RCLKE_c,
RE => RE_c,
WADDR => WADDR_c,
WCLK=> WCLK_c,
WCLKE => WCLKE_c,
WDATA => WDATA_c,
WE => WE_c
);
```

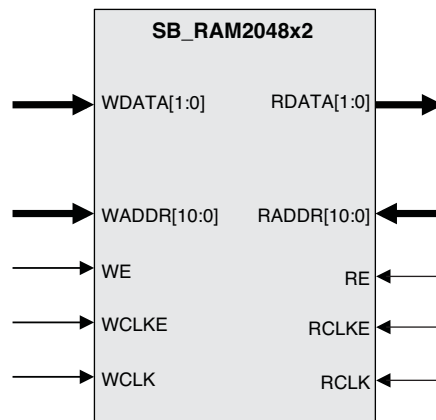
Table 6 is a complete list of SB\_RAM1024x4 based primitives.

**Table 6. SB\_RAM1024x4 Based Primitives**

| Primitive        | Description   |
|------------------|---|
| SB_RAM1024x4     | SB_RAM1024x4 //Positive edged clock RCLK WCLK (RDATA, RCLK, RCLKE, RE, RADDR, WCLK, WCLKE, WE, WADDR, MASK, WDATA);                           |
| SB_RAM1024x4NR   | SB_RAM1024x4NR // Negative edged Read Clock – i.e. RCLKN (RDATA, RCLKN, RCLKE, RE, RADDR, WCLK, WCLKE, WE, WADDR, MASK, WDATA);               |
| SB_RAM1024x4NW   | SB_RAM1024x4NW // Negative edged Write Clock – i.e. WCLKN (RDATA, RCLK, RCLKE, RE, RADDR, WCLKN, WCLKE, WE, WADDR, MASK, WDATA);              |
| SB_RAM1024x4NRNW | SB_RAM1024x4NRNW // Negative edged Read and Write – i.e. RCLKN WRCLKN (RDATA, RCLKN, RCLKE, RE, RADDR, WCLKN, WCLKE, WE, WADDR, MASK, WDATA); |

## SB\_RAM2048x2

**Figure 7. SB\_RAM2048x2**



## Verilog Instantiation

```
SB_RAM2048x2 ram2048x2_inst (
    .RDATA(RDATA_c[2:0]),
    .RADDR(RADDR_c[10:0]),
    .RCLK(RCLK_c),
    .RCLKE(RCLKE_c),
    .RE(RE_c),
    .WADDR(WADDR_c[2:0]),
    .WCLK(WCLK_c),
    .WCLKE(WCLKE_c),
    .WDATA(WDATA_c[10:0]),
    .WE(WE_c)
);
```

[illegible]

## VHDL Instantiation

```
Ram2048x2_inst : SB_RAM2048x2
```

[illegible]

```
port map (
  RDATA => RDATA_c,
  RADDR => RADDR_c,
  RCLK => RCLK_c,
  RCLKE => RCLKE_c,
  RE => RE_c,
  WADDR => WADDR_c,
  WCLK=> WCLK_c,
  WCLKE => WCLKE_c,
  WDATA => WDATA_c,
  WE => WE_c
);
```

Table 7 is a complete list of the SB\_RAM2048x2 based primitives.

**Table 7. SB\_RAM2048x2 Based Primitives**

| Primitive        | Description   |
|------------------|---|
| SB_RAM2048x2     | SB_RAM2048x2 //Positive edged clock RCLK WCLK (RDATA, RCLK, RCLKE, RE, RADDR, WCLK, WCLKE, WE, WADDR, MASK, WDATA);                           |
| SB_RAM2048x2NR   | SB_RAM2048x2NR // Negative edged Read Clock – i.e. RCLKN (RDATA, RCLKN, RCLKE, RE, RADDR, WCLK, WCLKE, WE, WADDR, MASK, WDATA);               |
| SB_RAM2048x2NW   | SB_RAM2048x2NW // Negative edged Write Clock – i.e. WCLKN (RDATA, RCLK, RCLKE, RE, RADDR, WCLKN, WCLKE, WE, WADDR, MASK, WDATA);              |
| SB_RAM2048x2NRNW | SB_RAM2048x2NRNW // Negative edged Read and Write – i.e. RCLKN WRCLKN (RDATA, RCLKN, RCLKE, RE, RADDR, WCLKN, WCLKE, WE, WADDR, MASK, WDATA); |

## SB\_RAM40\_4K

SB\_RAM40\_4K is the basic physical RAM primitive which can be instantiated and configured to different depths and data ports. The SB\_RAM40\_4K block has a size of 4 Kbits with separate write and read ports, each with independent control signals. By default, input and output data is 16 bits wide, although the data width is configurable using the READ\_MODE and WRITE\_MODE parameters. The data contents of the SB\_RAM40\_4K block are optionally pre-loaded during iCE device configuration.

**Table 8. SB\_RAM40\_4K Naming Convention Rules**

| RAM Primitive Name | Description   |
|--------------------|---|
| SB_RAM40_4K        | Positive-edged read clock, positive-edged write clock |
| SB_RAM40_4KNR      | Negative-edged read clock, positive-edged write clock |
| SB_RAM40_4KNW      | Positive-edged read clock, negative-edged write clock |
| SB_RAM40_4KNRNW    | Negative-edged clock, negative-edged write clock      |

**Figure 8. SB\_RAM40\_4K**

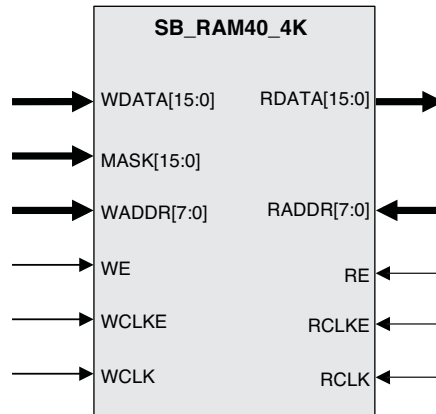


Table 9 lists the signals for both ports.

**Table 9. SB\_RAM40\_4K Signal Descriptions**

| Signal Name | Direction | Description   |
|-------------|-----------|---|
| WDATA[15:0] | Input     | Write Data input.   |
| MASK[15:0]  | Input     | Bit-line Write Enable input, active low. Applicable only when WRITE_MODE parameter is set to '0'. |
| WADDR[7:0]  | Input     | Write Address input. Selects up to 256 possible locations.  |
| WE          | Input     | Write Enable input, active high.  |
| WCLK        | Input     | Write Clock input, rising-edge active.  |
| WCLKE       | Input     | Write Clock Enable input.   |
| RDATA[15:0] | Output    | Read Data output.   |
| RADDR[7:0]  | Input     | Read Address input. Selects one of 256 possible locations.  |
| RE          | Input     | Read Enable input, active high.   |
| RCLK        | Input     | Read Clock input, rising-edge active.   |
| RCLKE       | Input     | Read Clock Enable input.  |

Table 10 describes the parameter values to infer the desired RAM configuration.

**Table 10. SB\_RAM40\_4K Primitive Parameter Descriptions**

| Parameter Name        | Description  | Parameter Value  | Configuration                            |
|-----------------------|--|------------------|--|
| INIT_0, ... ..,INIT_F | RAM Initialization Data. Passed using 16 parameter strings, each comprising 256 bits. (16 x 256=4096 total bits) | INIT_0 to INIT_F | Initialize the RAM with predefined value |
| WRITE_MODE            | Sets the RAM block write port configuration  | 0                | 256 x 16                                 |
|                       |  | 1                | 512 x 18                                 |
|                       |  | 2                | 1024 x 4                                 |
|                       |  | 3                | 2048 x 2                                 |
| READ_MODE             |  | 0                | 256 x 16                                 |
|                       |  | 1                | 512 x 8                                  |
|                       |  | 2                | 1024 x 4                                 |
|                       |  | 3                | 2048 x 2                                 |

---

**Verilog Instantiation**

```
// Physical RAM Instance without Pre Initialization
```

```
SB_RAM40_4K ram40_4kinst_physical (
```

```
    .RDATA(RDATA) ,  
    .RADDR(RADDR) ,  
    .WADDR(WADDR) ,  
    .MASK(MASK) ,  
    .WDATA(WDATA) ,  
    .RCLKE(RCLKE) ,  
    .RCLK(RCLK) ,  
    .RE(RE) ,  
    .WCLKE(WCLKE) ,  
    .WCLK(WCLK) ,  
    .WE(WE)
```

```
);
```

```
defparam ram40_4kinst_physical.READ_MODE=0;
```

```
defparam ram40_4kinst_physical.WRITE_MODE=0;
```

**VHDL Instantiation**

```
-- Physical RAM Instance without Pre Initialization
```

```
ram40_4kinst_physical : SB_RAM40_4K
```

```
generic map (  
    READ_MODE => 0 ,  
    WRITE_MODE => 0  
)
```

```
port map (  
    RDATA=>RDATA ,  
    RADDR=>RADDR ,  
    WADDR=>WADDR ,  
    MASK=>MASK ,  
    WDATA=>WDATA ,  
    RCLKE=>RCLKE ,  
    RCLK=>RCLK ,  
    RE=>RE ,  
    WCLKE=>WCLKE ,  
    WCLK=>WCLK ,  
    WE=>WE
```

```
);
```

**EBR Utilization Summary in iCEcube2 Design Software**

The placer.log file in the iCEcube2 design software shows the device utilization summary. The Final Design Statistics and Device Utilization Summary sections show the number of EBRs (or RAMs) used against the total number. Figure 9 shows the EBR usage when one SB\_RAM256x16 was instantiated in the design.



Figure 9. iCEcube2 Design Software Report File

```

Device/Operating Condition
└─ Device Info
    DeviceFamily    iCE40
    Device          LP8K
    Device Package  CM121
    Power Grade
└─ Operating Condition
    Core Voltage(V) 1.14
    Temperature(C)  70

Final Design Statistics
Number of LUTs      : 0
Number of DFFs     : 0
Number of Carrys    : 0
Number of RAMs     : 1
Number of ROMs     : 0
Number of IOs      : 68
Number of GBIOs    : 2
Number of GBs      : 0
Number of WarmBoot : 0
Number of PLLs     : 0
Number of MIPIs    : 0
Number of HDMIs    : 0

Device Utilization Summary
LogicCells          : 0/7680
PLRs               : 0/960
BRAMs              : 1/32
IOs and GBIOs      : 70/93

I2054: Placement of design completed successfully
I2076: Placer run-time: 0.9 sec.

```

## Technical Support Assistance

e-mail: [techsupport@latticesemi.com](mailto:techsupport@latticesemi.com)

Internet: [www.latticesemi.com](http://www.latticesemi.com)

## Revision History

| Date           | Version | Change Summary  |
|----------------|---------|---|
| January 2015   | 1.4     | Added support for iCE40 UltraLite.  |
| June 2014      | 01.3    | Added support for iCE40 Ultra.  |
| December 2013  | 01.2    | Added information to EBR Signal Descriptions table.                                   |
| October 2013   | 01.1    | Removed iCE40 Family EBRs table.<br>Updated Technical Support Assistance information. |
| September 2012 | 01.0    | Initial release.  |

---

## Appendix A. Standard HDL Code References

This appendix contains standard HDL (Verilog and VHDL) codes for popular memory elements, which can be used to infer a sysMEM EBR automatically. Standard HDL coding techniques do not require you to know the details of the Block RAMs of the device and are inferred automatically.

### Single-Port RAM

#### Verilog

```
module ram (din, addr, write_en, clk, dout); // 512x8
    parameter addr_width = 9;
    parameter data_width = 8;
    input [addr_width-1:0] addr;
    input [data_width-1:0] din;
    input write_en, clk;
    output [data_width-1:0] dout;
    reg [data_width-1:0] dout; // Register for output.
    reg [data_width-1:0] mem [(1<<addr_width)-1:0];

    always @(posedge clk)
    begin
        if (write_en)
            mem[(addr)] <= din;
        dout = mem[addr]; // Output register controlled by clock.
    end
endmodule
```

#### VHDL

```
library IEEE;
use IEEE.std_logic_1164.all;
use IEEE.std_logic_unsigned.all;

entity ram is
    generic (
        addr_width : natural := 9; -- 512x8
        data_width : natural := 8);
    port (
        addr : in  std_logic_vector (addr_width - 1 downto 0);
        write_en : in  std_logic;
        clk : in  std_logic;
        din : in  std_logic_vector (data_width - 1 downto 0);
        dout : out std_logic_vector (data_width - 1 downto 0));
end ram;

architecture rtl of ram is
    type mem_type is array ((2** addr_width) - 1 downto 0) of
        std_logic_vector(data_width - 1 downto 0);
    signal mem : mem_type;
begin
    process (clk)
    begin
        if (clk'event and clk = '1') then
            if (write_en = '1') then
                mem(conv_integer(addr)) <= din;
            end if;
        end if;
    end process;
end architecture;
```

```
        dout <= mem(conv_integer(addr));
    end if;

    -- Output register controlled by clock.
end process;
end rtl;
```

## Dual Port Ram

### Verilog

```
module ram (din, write_en, waddr, wclk, raddr, rclk, dout); //512x8
    parameter addr_width = 9;
    parameter data_width = 8;
    input [addr_width-1:0] waddr, raddr;
    input [data_width-1:0] din;
    input write_en, wclk, rclk;
    output reg [data_width-1:0] dout;
    reg [data_width-1:0] mem [(1<<addr_width)-1:0]
        ;

    always @(posedge wclk) // Write memory.
    begin
        if (write_en)
            mem[waddr] <= din; // Using write address bus.
        end
    always @(posedge rclk) // Read memory.
    begin
        dout <= mem[raddr]; // Using read address bus.
    end
endmodule
```

### VHDL

```
library IEEE;
use IEEE.std_logic_1164.all;
use IEEE.std_logic_unsigned.all;

entity ram is
    generic (
        addr_width : natural := 9; --512x8
        data_width : natural := 8);
    port (
        write_en : in std_logic;
        waddr : in std_logic_vector (addr_width - 1 downto 0);
        wclk : in std_logic;
        raddr : in std_logic_vector (addr_width - 1 downto 0);
        rclk : in std_logic;
        din : in std_logic_vector (data_width - 1 downto 0);
        dout : out std_logic_vector (data_width - 1 downto 0));
end ram;

architecture rtl of ram is
    type mem_type is array ((2** addr_width) - 1 downto 0) of
        std_logic_vector(data_width - 1 downto 0);
    signal mem : mem_type;
```

```
begin
  process (wclk)
    -- Write memory.
    begin
      if (wclk'event and wclk = '1') then
        if (write_en = '1') then
          mem(conv_integer(waddr)) <= din;
          -- Using write address bus.
        end if;
      end if;
    end process;
  process (rclk) -- Read memory.
    begin
      if (rclk'event and rclk = '1') then
        dout <= mem(conv_integer(raddr));
        -- Using read address bus.
      end if;
    end process;
end rtl;
```